

Amendments to the Specification:

Please replace the paragraph at 1, line 5 to line 15 with the following new paragraph:

This application claims the benefit of U.S. Provisional Patent Application No. 60/469,433 filed May 9, 2003 naming Tipton et al. and titled "Method of Porogen Removal from Porous Low-K Films Using UV Irradiation," and this This application is a continuation-in-part claiming priority under 35 USC 120 from US Patent Application No. 10/404,693, filed on March 31, 2003, titled "Method for Forming Porous Films by Porogen Removal Combined with In Situ Surface Modification," by Raashina Humayun et al. as inventors, ~~which application is~~ Both applications are incorporated herein by reference in their entireties ~~its entirety~~ for all purposes. This application is also related to US Patent Application No. 10/672,305 _____ (~~Attorney Docket NOVLP069~~) filed on the same day as the instant application, titled "Method for Removal of Porogens from Porous Low-k Films Using Supercritical Fluids," by Adrienne Tipton et al. as inventors and to US Patent Application No. 10/295,965 filed November 15, 2002 by Schulberg, et al., and titled "System for Deposition of Mesoporous Materials," which applications are incorporated herein by reference in its entirety for all purposes.